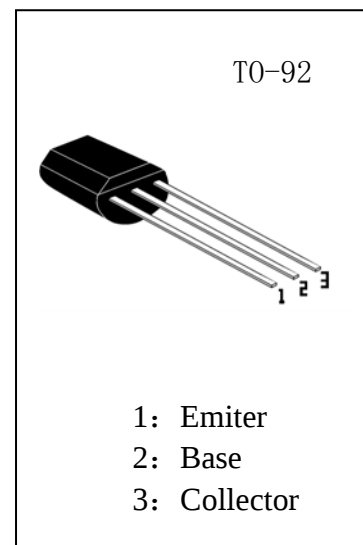


## 低压晶体管

- 高集电极电流  $I_c=1200\text{mA}$
- 高耗散功率  $P_c=1000\text{mW}$
- 与 8550 对管

## 极限参数(Absolute Maximum Ratings) $T_a=25^\circ\text{C}$

| Characteristic            | Symbol    | Rating         | Unit             |
|---------------------------|-----------|----------------|------------------|
| Collector-Base Voltage    | $V_{cbo}$ | <b>40</b>      | V                |
| Collector-Emitter Voltage | $V_{ceo}$ | <b>25</b>      | V                |
| Emitter-Base Voltage      | $V_{ebo}$ | <b>6</b>       | V                |
| Collector Current         | $I_c$     | <b>1200</b>    | mA               |
| Collector Dissipation     | $P_c$     | <b>1000</b>    | m W              |
| Junction Temperature      | $T_j$     | <b>150</b>     | $^\circ\text{C}$ |
| Storage Temperature       | $T_{stg}$ | <b>-55~150</b> | $^\circ\text{C}$ |



## 电性能(Electrical Characteristic) $T_a=25^\circ\text{C}$

| Symbol        | Characteristic                       | Test Condition                                  | Min | Typ  | Max | Unit          |
|---------------|--------------------------------------|-------------------------------------------------|-----|------|-----|---------------|
| $BV_{cbo}$    | Collector-Base Breakdown Voltage     | $I_c=100\mu\text{A}$ $I_e=0$                    | 40  |      |     | V             |
| $BV_{ceo}$    | Collector-Emitter Breakdown Voltage  | $I_c=2\text{mA}$ $I_b=0$                        | 25  |      |     | V             |
| $BV_{ebo}$    | Emitter-Base Breakdown Voltage       | $I_e=100\mu\text{A}$ $I_c=0$                    | 6   |      |     | V             |
| $I_{cbo}$     | Collector Cutoff Current             | $V_{cb}=35\text{V}$ , $I_e=0$                   |     |      | 100 | nA            |
| $I_{ebo}$     | Emitter Cutoff Current               | $V_{eb}=6\text{V}$ , $I_c=0$                    |     |      | 100 | nA            |
| $I_{ceo}$     | Collector Cutoff Current             | $V_{ce}=25\text{V}$ , $I_b=0$                   |     |      | 10  | $\mu\text{A}$ |
| $V_{ce(sat)}$ | Collector-Emitter Saturation Voltage | $I_c=800\text{mA}$ , $I_b=80\text{mA}$          |     | 0.26 | 0.5 | V             |
| $V_{be(sat)}$ | Base-Emitter Saturation Voltage      | $I_c=800\text{mA}$ , $I_b=80\text{mA}$          |     | 0.98 | 1.2 | V             |
| $V_{be(on)}$  | Base-Emitter On Voltage              | $V_{ce}=1\text{V}$ , $I_c=10\text{mA}$          |     | 0.66 | 1   | V             |
| $H_{fe1}$     | DC Current Gain                      | $V_{ce}=1\text{V}$ , $I_c=5\text{mA}$           | 45  |      |     |               |
| $H_{fe2}$     | DC Current Gain                      | $V_{ce}=1\text{V}$ , $I_c=100\text{mA}$         | 85  |      | 400 |               |
| $H_{fe3}$     | DC Current Gain                      | $V_{ce}=1\text{V}$ , $I_c=800\text{mA}$         | 30  |      |     |               |
| $C_{ob}$      | Output Capacitance                   | $V_{cb}=10\text{V}$ , $I_e=0$ , $f=1\text{MHz}$ |     | 9    | 15  | PF            |
| $f_T$         | Current Gain-Bandwidth product       | $V_{ce}=10\text{V}$ , $I_c=50\text{mA}$ ,       | 100 | 200  |     | MHz           |

| CLASS       | B      | C           | D       |         |         |         |         |
|-------------|--------|-------------|---------|---------|---------|---------|---------|
| <b>Hfe2</b> | 85-120 | 120-160-200 | 160-200 | 200-250 | 250-300 | 300-350 | 350-400 |